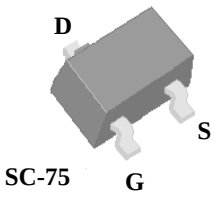
AP1332GEV-HF

Halogen-Free Product

Advanced Power Electronics Corp.

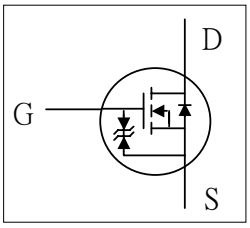
N-CHANNEL ENHANCEMENT MODE POWER MOSFET

- ▼ **Lower Gate Charge**
- ▼ **Gate Pateded Diode**
- ▼ **Small Package Outline**
- ▼ **RoHS Compliant & Halogen-Free**



SC-75

BV_{DSS}	20V
$R_{DS(ON)}$	0.9Ω
I_D	450mA



Description

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, low on-resistance and cost-effectiveness.

SC-75 with 1.6x1.6mm very small footprint and suited for hand held applications.

Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	±6	V
I_D@T_A=25℃	Continuous Drain Current[3]	450	mA
I_D@T_A=70℃	Continuous Drain Current[3]	360	mA
I_{DM}	Pulsed Drain Current[1]	1	A
P_D@T_A=25℃	Total Power Dissipation	0.35	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Value	Unit
Rthj-a	Maximum Thermal Resistance, Junction-ambient[3]	420	℃/W

Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250uA	20	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=4.5V, I_D=400mA	-	-	0.9	Ω
		V_{GS}=2.5V, I_D=300mA	-	-	1	Ω
		V_{GS}=1.8V, I_D=200mA	-	-	1.5	Ω
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250uA	0.25	-	1	V
g_{fs}	Forward Transconductance	V_{DS}=5V, I_D=400mA	-	1.3	-	S
I_{DSS}	Drain-Source Leakage Current	V_{DS}=16V, V_{GS}=0V	-	-	10	uA
I_{GSS}	Gate-Source Leakage	V_{GS}=±6V, V_{DS}=0V	-	-	±30	uA
Q_g	Total Gate Charge	I_D=400mA	-	1.2	1.9	nC
Q_{gs}	Gate-Source Charge	V_{DS}=10V	-	0.3	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	V_{GS}=4.5V	-	0.3	-	nC
$t_{d(on)}$	Turn-on Delay Time	V_{DS}=10V	-	18	-	ns
t_r	Rise Time	I_D=400mA	-	34	-	ns
$t_{d(off)}$	Turn-off Delay Time	R_G=3.3Ω	-	110	-	ns
t_f	Fall Time	V_{GS}=5V	-	115	-	ns
C_{iss}	Input Capacitance	V_{GS}=0V	-	45	72	pF
C_{oss}	Output Capacitance	V_{DS}=10V	-	22	-	pF
C_{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	12	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_{SD}	Forward On Voltage[2]	I_S=300mA, V_{GS}=0V	-	-	1.2	V

Notes:

1.Pulse width limited by Max. junction temperature.

2.Pulse test.

3.Surface mounted on FR4 board.

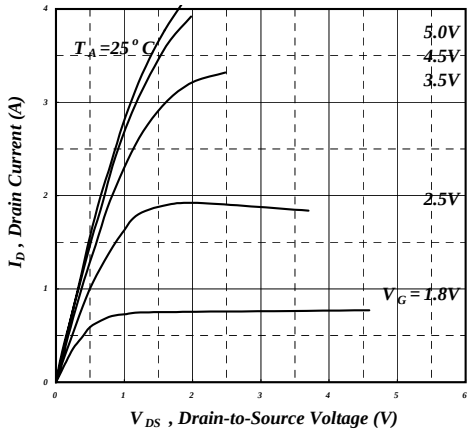


Fig 1. Typical Output Characteristics

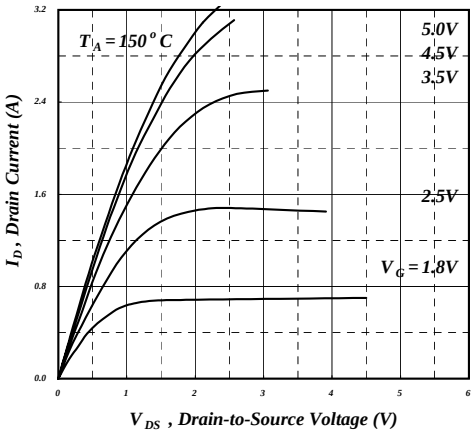


Fig 2. Typical Output Characteristics

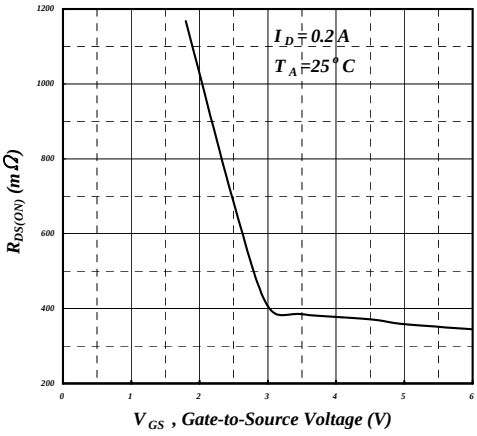


Fig 3. On-Resistance v.s. Gate Voltage

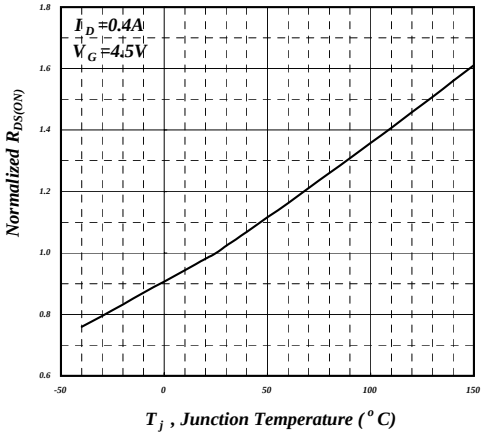


Fig 4. Normalized On-Resistance v.s. Junction Temperature

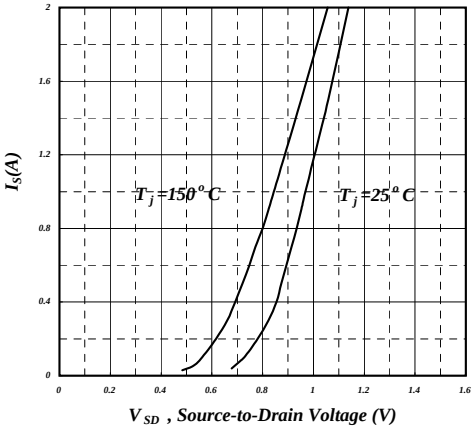


Fig 5. Forward Characteristic of Reverse Diode

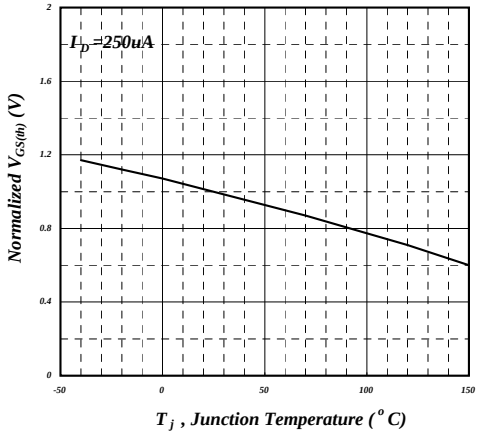


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

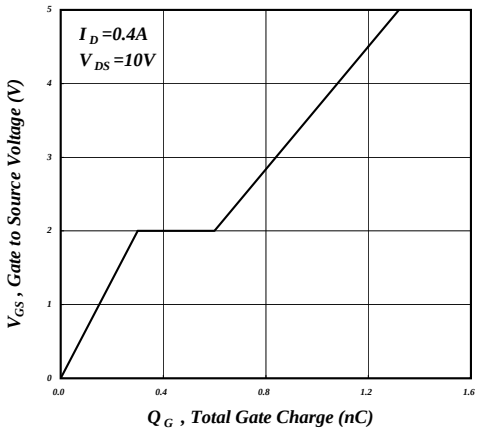


Fig 7. Gate Charge Characteristics

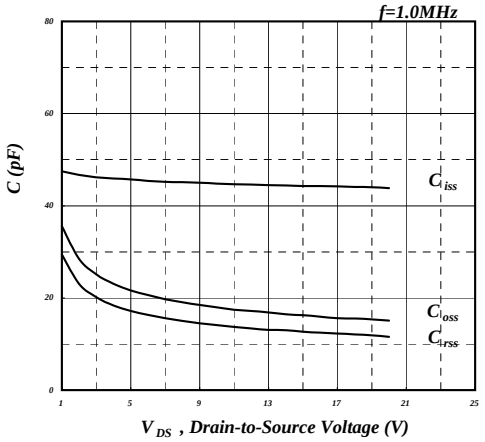


Fig 8. Typical Capacitance Characteristics

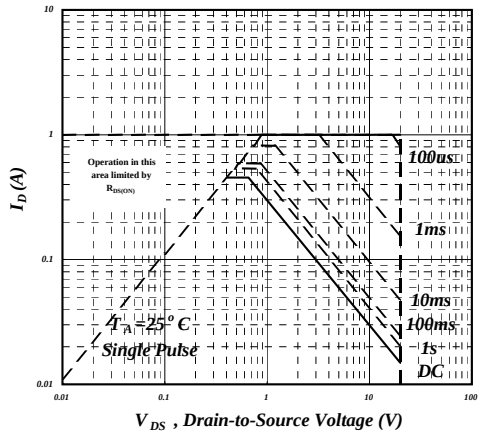


Fig 9. Maximum Safe Operating Area

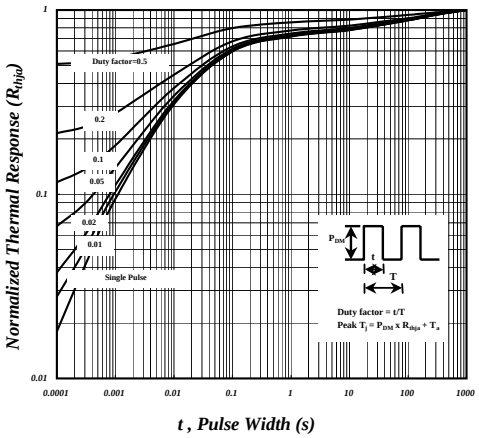


Fig 10. Effective Transient Thermal Impedance

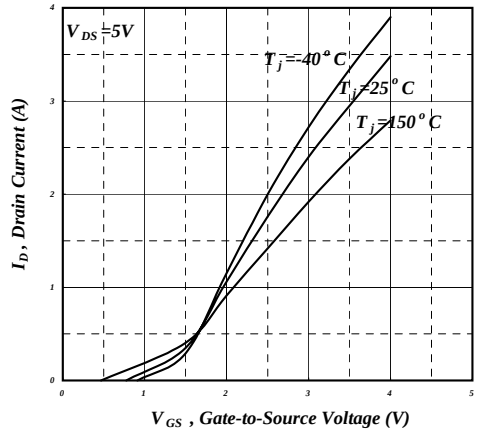


Fig 11. Transfer Characteristics

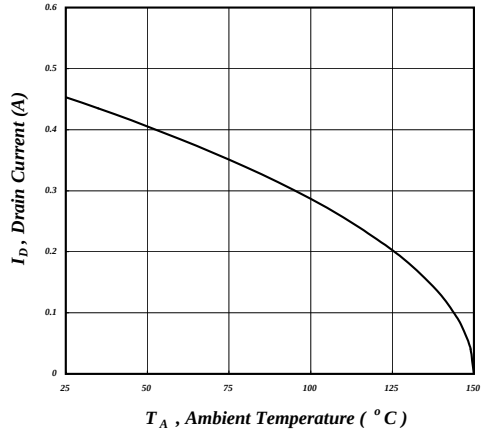


Fig 12. Maximum Continuous Drain Current v.s. Ambient Temperature